# **1SS119**

Silicon Epitaxial Planar Diode for High Speed Switching

# **HITACHI**

ADE-208-180A (Z) Rev. 1 Aug. 1995

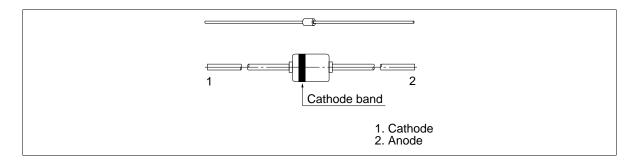
#### **Features**

- Low capacitance. (C = 3.0pF max)
- Short reverse recovery time.  $(t_{rr} = 3.5 \text{ns max})$
- Small glass package (MHD) enables easy mounting and high reliability.

### **Ordering Information**

Type No.	Cathode band	Package Code
1SS119	Light Blue	MHD

#### **Outline**





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## **Absolute Maximum Ratings** $(Ta = 25^{\circ}C)$

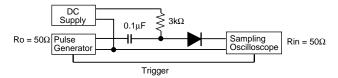
Item	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}$	35	V
Reverse voltage	V <sub>R</sub>	30	V
Peak forward current	I <sub>FM</sub>	450	mA
Non-Repetitive peak forward surge current	I <sub>FSM</sub> *	1	А
Average forward current	Io	150	mA
Power dissipation	Pd	250	mW
Junction temperature	Tj	175	°C
Storage temperature	Tstg	-65 to +175	°C

Note: Within 1s forward surge current.

## **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	$V_{F}$	_	_	8.0	V	$I_F = 10mA$
Reverse current	$I_R$	_	_	0.1	μΑ	V <sub>R</sub> = 30V
Capacitance	С	_	_	3.0	pF	V <sub>R</sub> = 1V, f = 1MHz
Reverse recovery time	t <sub>rr</sub> *	_	_	3.5	ns	$I_F = 10 \text{mA}, V_R = 6 \text{V}, R_L = 50 \Omega$

Note: Reverse recovery time test circuit



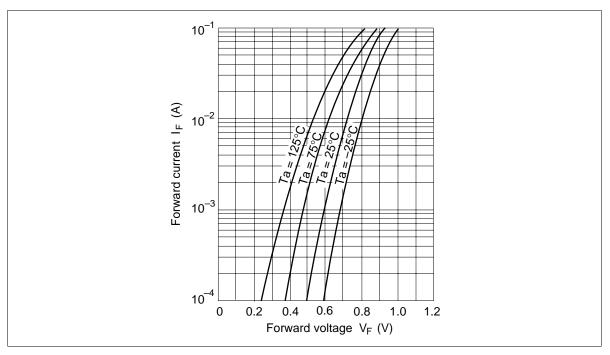


Fig.1 Forward current Vs. Forward voltage

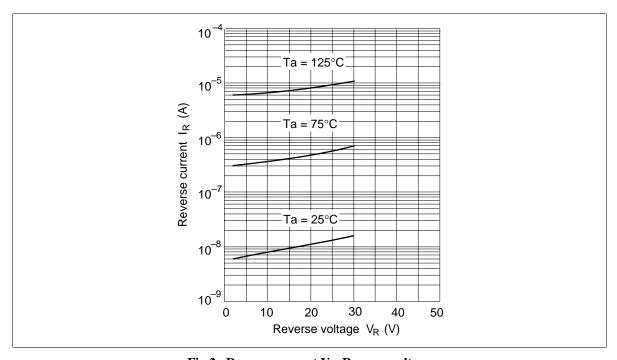


Fig.2 Reverse current Vs. Reverse voltage

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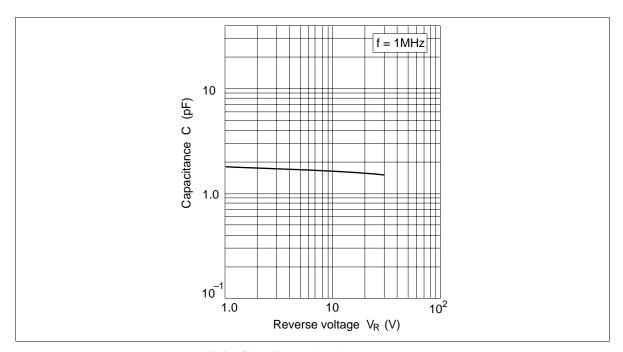
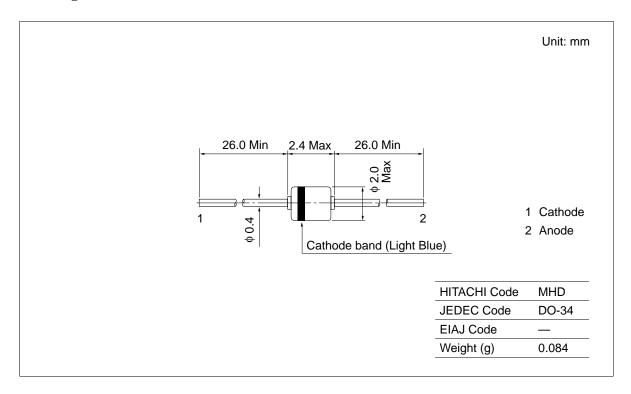


Fig.3 Capacitance Vs. Reverse voltage

## **Package Dimensions**



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Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Öhte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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#### For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive. San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group D-85622 Feldkirchen, Munich Germany

Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd.

Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead

Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281

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Telex: 40815 HITEC HX